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(12) **United States Design Patent**
Vinciarelli et al.

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- (54) **SEMICONDUCTOR DEVICE**
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- (72) Inventors: **Patrizio Vinciarelli**, Boston, MA (US);
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- (73) Assignee: **VLT, Inc.**, Sunnyvale, CA (US)
- (**) Term: **14 Years**
- (21) Appl. No.: **29/448,057**
- (22) Filed: **Mar. 8, 2013**

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Related U.S. Application Data

- (63) Continuation-in-part of application No. 13/789,065, filed on Mar. 7, 2013.
- (51) **LOC (10) Cl.** **13-03**
- (52) **U.S. Cl.**
USPC **D13/182**
- (58) **Field of Classification Search**
USPC D13/110, 182; 257/668, 678, 690;
361/679.01, 713, 728, 736, 760, 761,
361/775, 820; 324/71.5, 252; 174/250, 253;
438/64, 65, 66
See application file for complete search history.

(57) **CLAIM**
We claim the ornamental design for a semiconductor device, as shown and described.

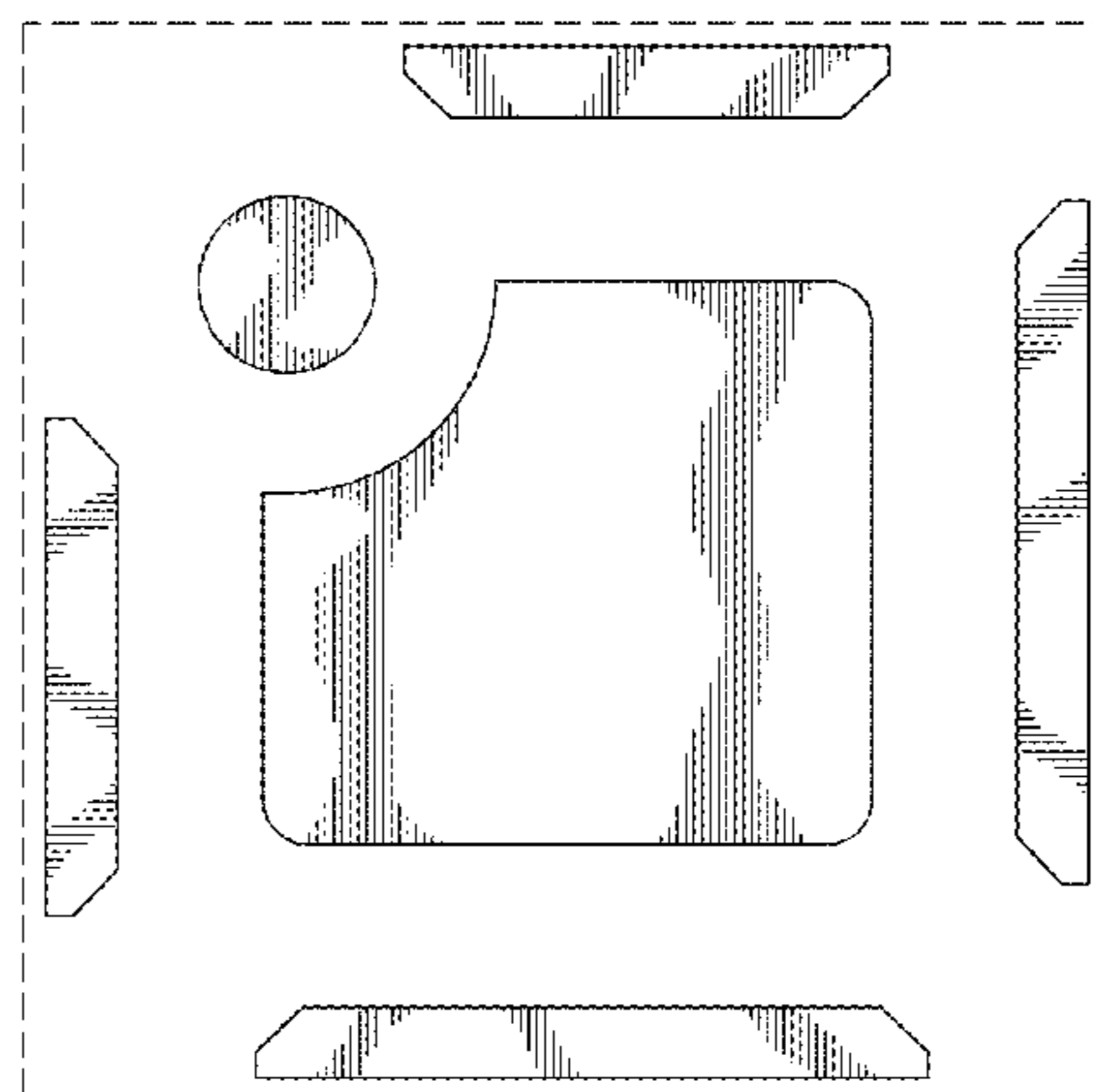
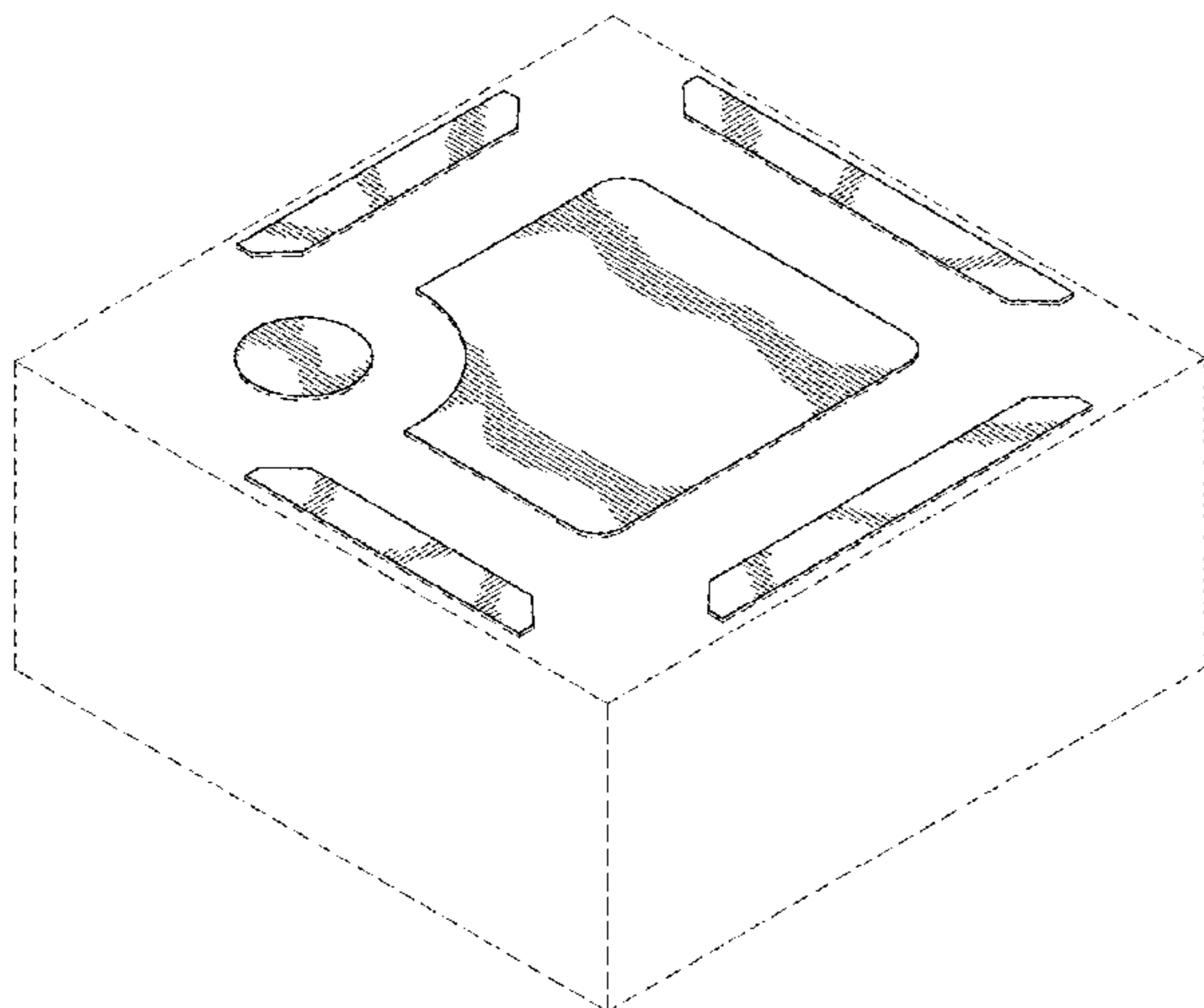
DESCRIPTION

FIG. 1 is a perspective view of a first embodiment of a semiconductor device showing our new design;
 FIG. 2 is a top plan view thereof;
 FIG. 3 is a bottom plan view thereof;
 FIG. 4 is a front elevation view thereof;
 FIG. 5 is a rear elevation view thereof;
 FIG. 6 is a right side elevation view thereof;
 FIG. 7 is a left side elevation view thereof;
 FIG. 8 is a perspective view of a second embodiment of a semiconductor device showing our new design;
 FIG. 9 is a top plan view thereof;
 FIG. 10 is a bottom plan view thereof;
 FIG. 11 is a front elevation view thereof;
 FIG. 12 is a rear elevation view thereof;
 FIG. 13 is a right side elevation view thereof; and,
 FIG. 14 is a left side elevation view thereof.

The broken lines shown in the drawings represent portions of the semiconductor device that form no part of the claimed design.

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1 Claim, 10 Drawing Sheets



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Fig. 1

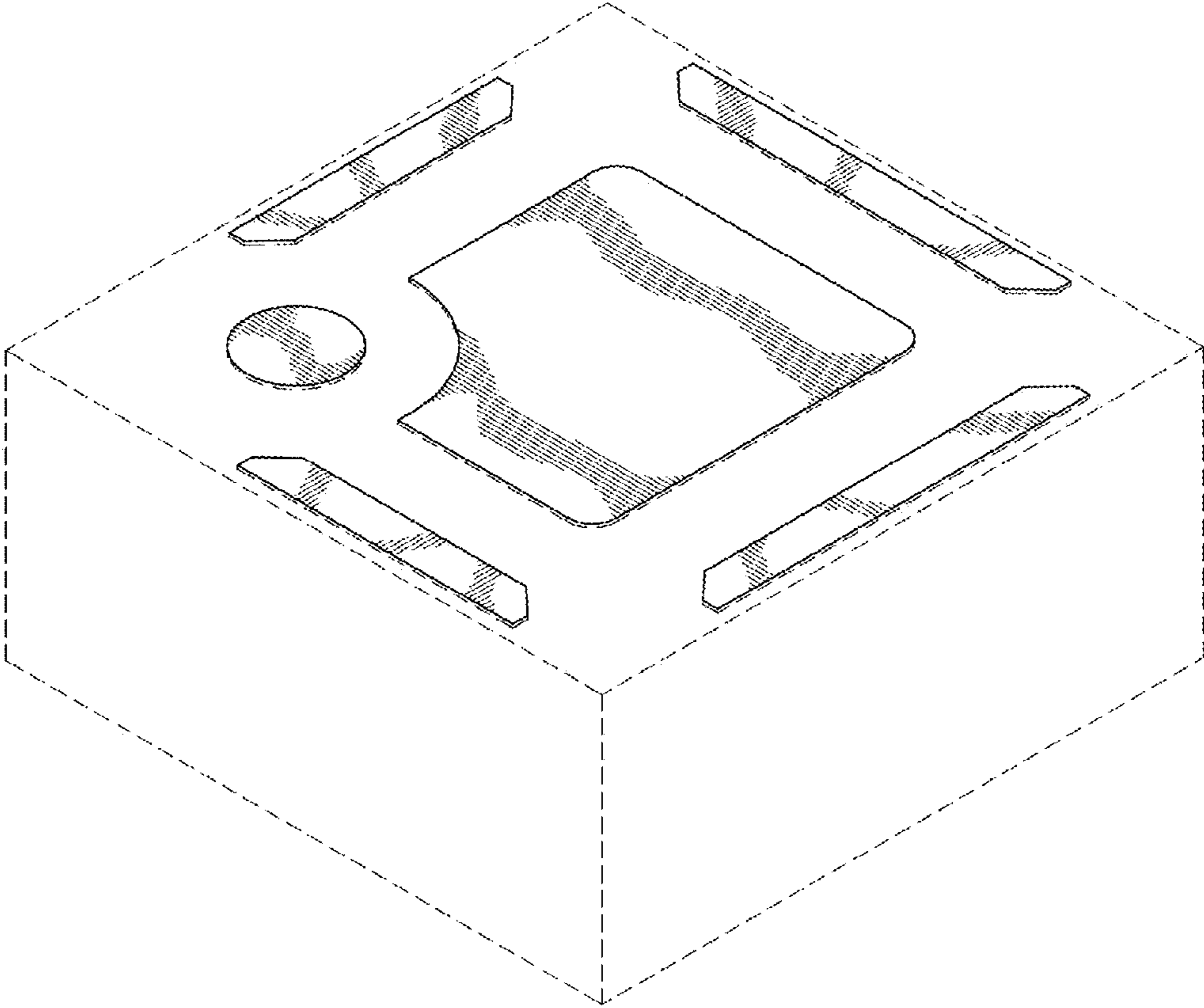


Fig. 2

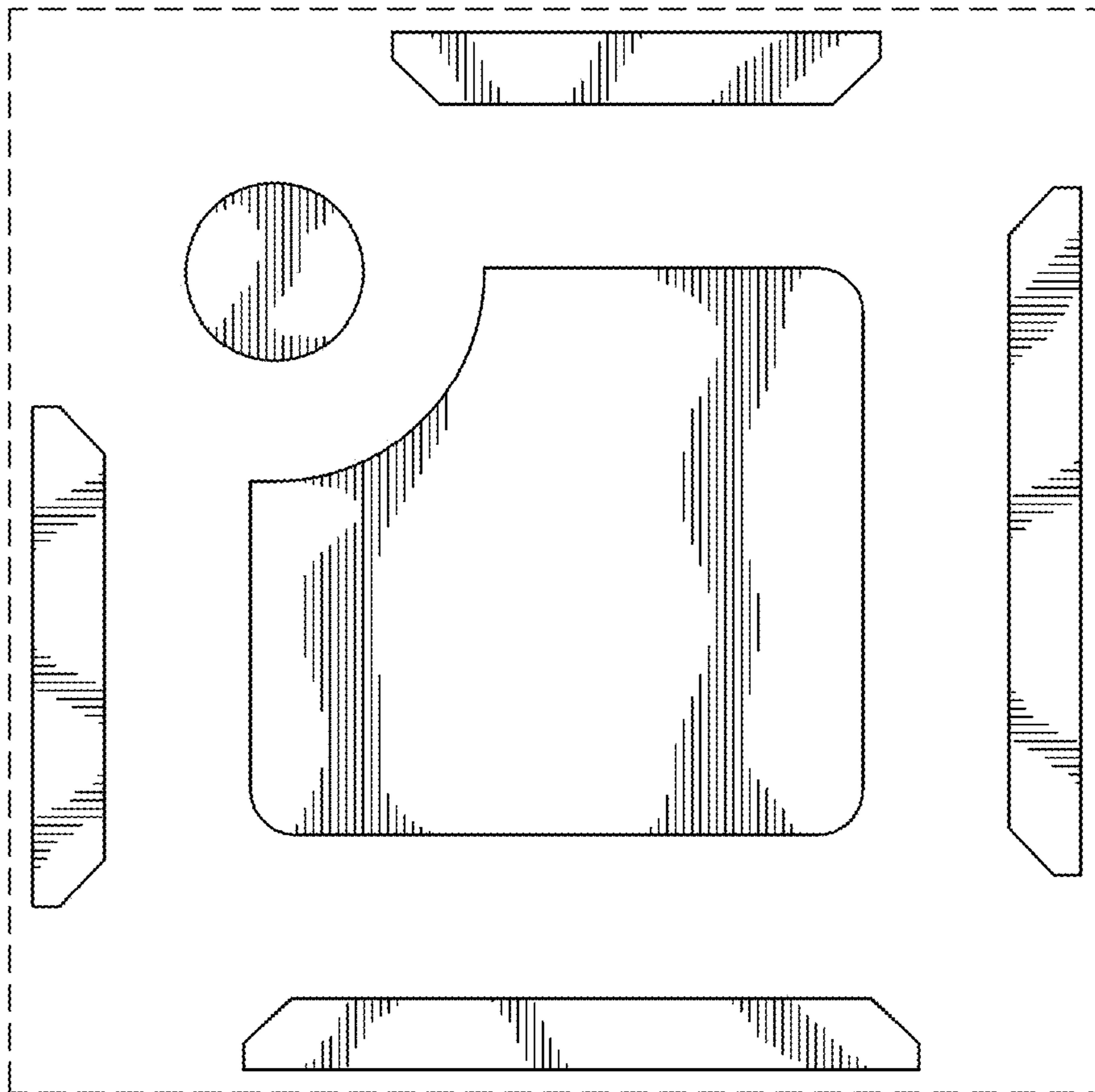


Fig. 3



Fig. 4



Fig. 5



Fig. 6



Fig. 7



Fig. 8

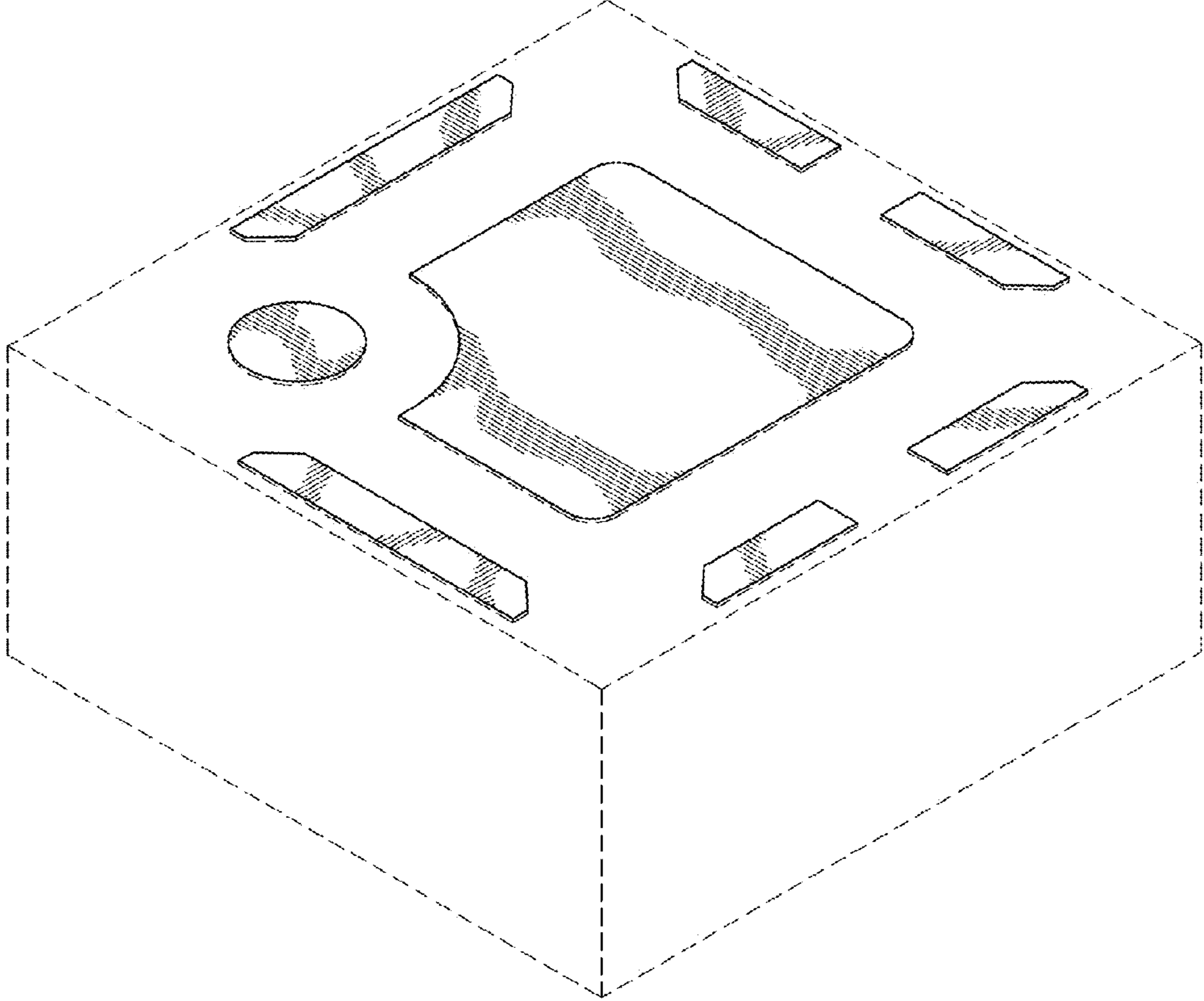


Fig. 9

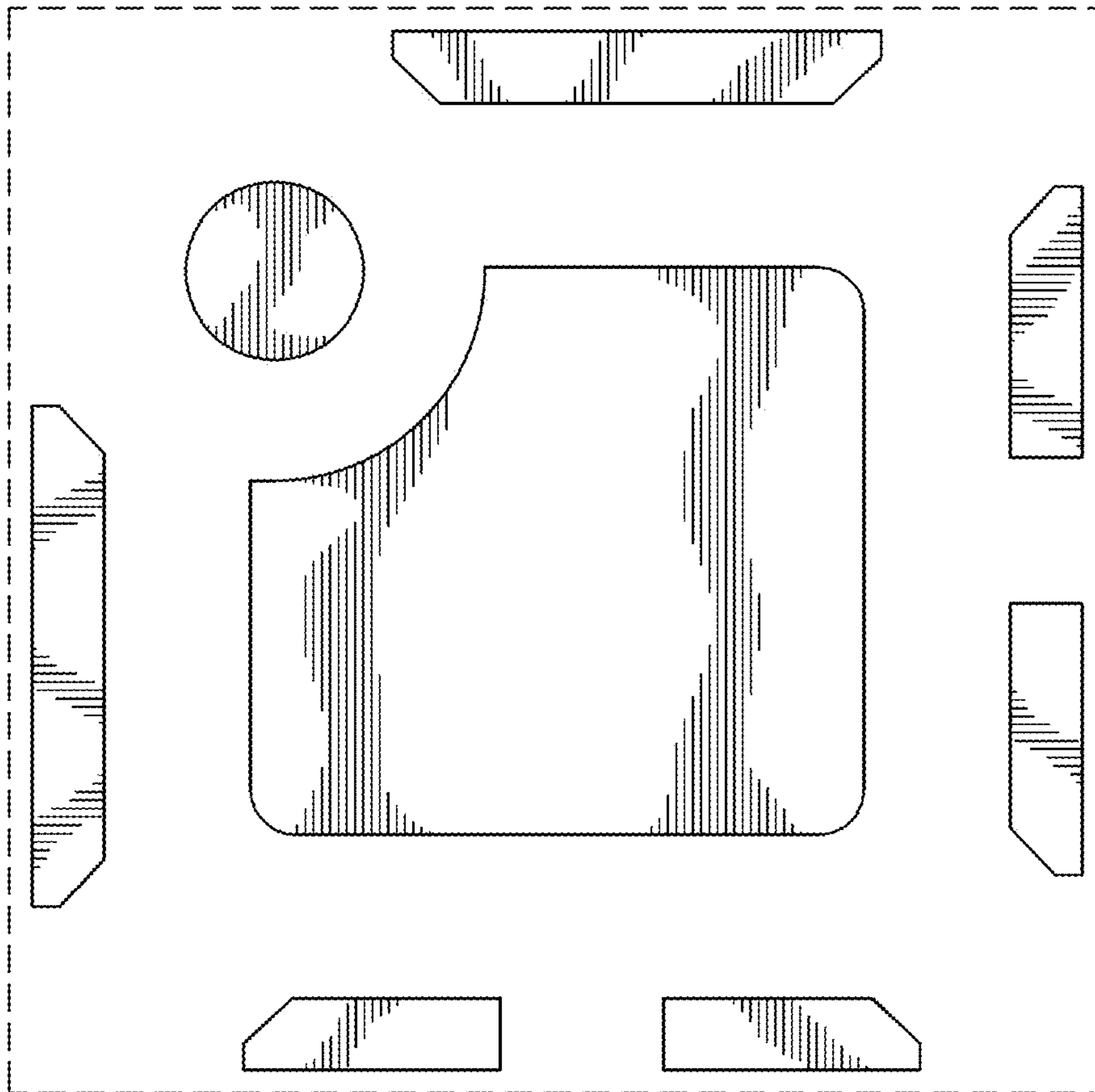


Fig. 10

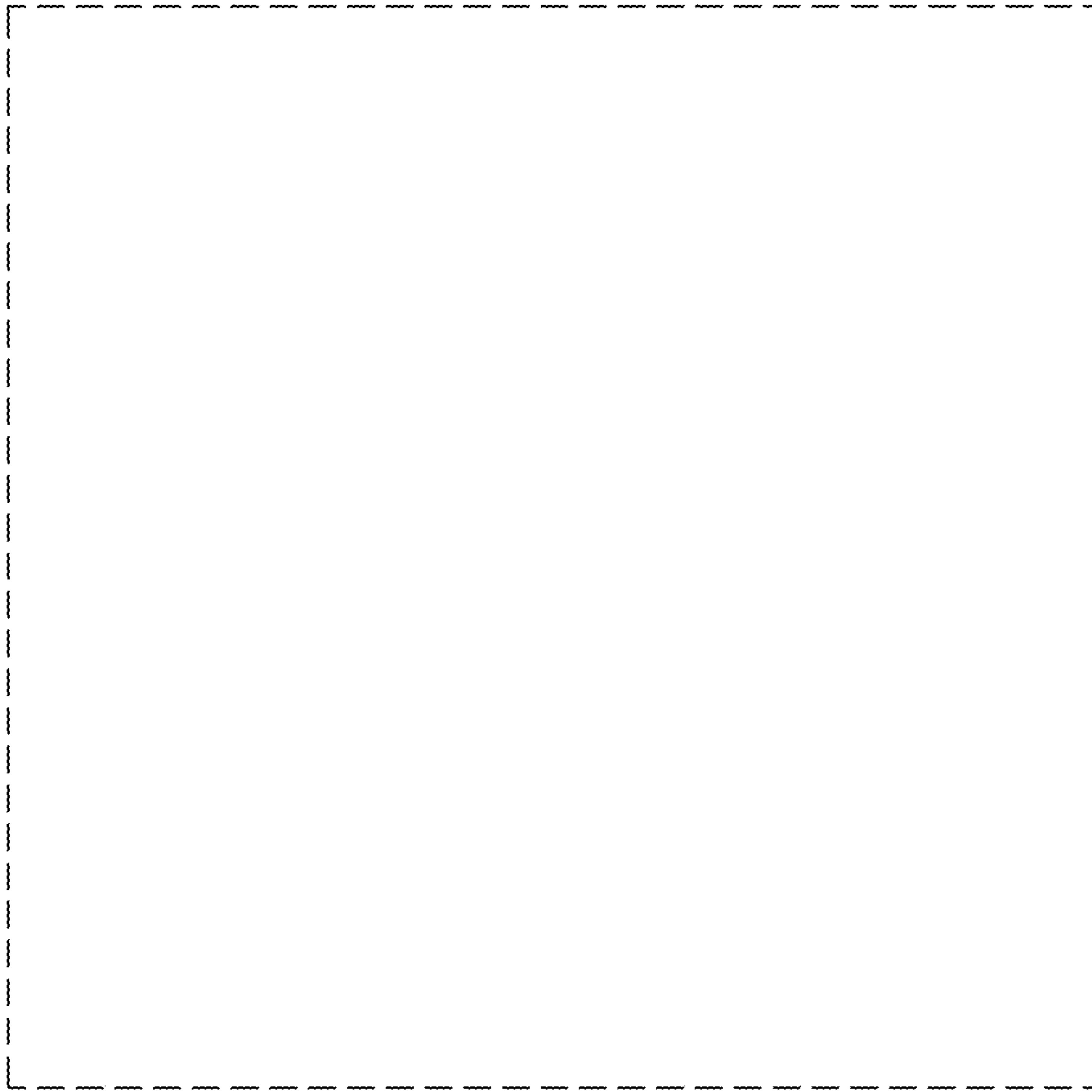


Fig. 11



Fig. 12



Fig. 13



Fig. 14

